

INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				<i>Complete if Known</i>	
Sheet	A1	of	A1	Application Number	10/560,488
				Filing Date	December 12, 2005
				First Named Inventor	Gerald Lucovsky
				Confirmation No.	3119
				Examiner Name	Benjamin P. Sandvik
				Attorney Docket Number	5051-639

OTHER NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
	2.	Woo Sik Kim: <i>Ferroelectric-gate field effect transistors using Nd₂Ti₂O₇/Y₂O₃/Si structures</i> ; <i>Thin Solid Films</i> 398-399 (2001) 663-667.	
	3.	Seung-Gu Lim; <i>Dielectric functions and optical bandgaps of high-K dielectrics for metal-oxide-semiconductor field-effect transistors by far ultraviolet spectroscopic ellipsometry</i> ; <i>Journal of Applied Physics</i> , Volume: 91, Number 7, pp 4500-4505 (April 1, 2002).	
	4.	J.K. Yamamoto; <i>Microwave dielectric properties of layered perovskite A₂B₂O₇ single-crystal fibers</i> ; <i>Elsevier Science Publishers B.V. (North-Holland (1991) Material Letters No. 11/12 pp 497-500.</i>	
	5.	European communication with European Search Report for Application No. 04776548.2 – 1235 PCT/US2004018863, dated 5-6-2008.	

Examiner Signature	/Benjamin Sandvik/ (09/03/2008)	Date Considered	
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if

not in conformance with the **REFERENCE CONDITIONS** specified in its **Technical Specification**.

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /B.S./